

CITATION REPORT

List of articles citing

Near-zero hysteresis and near-ideal subthreshold swing in h-BN encapsulated single-layer MoS₂ field-effect transistors

DOI: 10.1088/2053-1583/aab672
2D Materials, 2018, 5, 031001.

Source: <https://exaly.com/paper-pdf/69423151/citation-report.pdf>

Version: 2024-04-24

This report has been generated based on the citations recorded by exaly.com for the above article. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

#	Paper	IF	Citations
84	Single Crystal Growth of Millimeter-Sized Monoisotopic Hexagonal Boron Nitride. <i>Chemistry of Materials</i> , 2018 , 30, 6222-6225	9.6	63
83	Synthesis of hexagonal boron nitride heterostructures for 2D van der Waals electronics. <i>Chemical Society Reviews</i> , 2018 , 47, 6342-6369	58.5	80
82	Electronics and Optoelectronics Based on Two-Dimensional Materials. <i>Journal of the Korean Physical Society</i> , 2018 , 73, 1-15	0.6	8
81	Van der Waals heterostructures for optoelectronics: Progress and prospects. <i>Applied Materials Today</i> , 2019 , 16, 435-455	6.6	62
80	Tunable Negative Differential Resistance in van der Waals Heterostructures at Room Temperature by Tailoring the Interface. <i>ACS Nano</i> , 2019 , 13, 8193-8201	16.7	43
79	Multilevel MoS Optical Memory with Photoresponsive Top Floating Gates. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 25306-25312	9.5	41
78	Full Energy Spectra of Interface State Densities for n- and p-type MoS ₂ Field-Effect Transistors. <i>Advanced Functional Materials</i> , 2019 , 29, 1904465	15.6	20
77	Impact of Heat Treatment on a Hetero-Stacked MoS ₂ / h-BN Field-Effect Transistor. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1626-1629	4.4	1
76	Hexagonal Boron Nitride for Surface Passivation of Two-Dimensional van der Waals Heterojunction Solar Cells. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 39765-39771	9.5	21
75	A novel sonogel based on h-BN nanosheets for the tribological application under extreme conditions. <i>Tribology International</i> , 2019 , 138, 271-278	4.9	6
74	Influence of solid-state electrolyte on 2D SnS ₂ field effect transistors. <i>Materials Research Express</i> , 2019 , 6, 086320	1.7	3
73	High-Performance Monolayer MoS ₂ Films at the Wafer Scale by Two-Step Growth. <i>Advanced Functional Materials</i> , 2019 , 29, 1901070	15.6	24
72	Monolayer MoS Nanoribbon Transistors Fabricated by Scanning Probe Lithography. <i>Nano Letters</i> , 2019 , 19, 2092-2098	11.5	33
71	Hysteresis-Free Hexagonal Boron Nitride Encapsulated 2D Semiconductor Transistors, NMOS and CMOS Inverters. <i>Advanced Electronic Materials</i> , 2019 , 5, 1800419	6.4	17
70	Ultrashort Vertical-Channel van der Waals Semiconductor Transistors. <i>Advanced Science</i> , 2020 , 7, 1902964	4.6	10
69	Direct observation of the hysteretic Fermi level modulation in monolayer MoS ₂ field effect transistors. <i>Current Applied Physics</i> , 2020 , 20, 298-303	2.6	6
68	Vertical Integration of 2D Building Blocks for All-2D Electronics. <i>Advanced Electronic Materials</i> , 2020 , 6, 2000550	6.4	10

67	Humidity-Dependent Characteristics of Few-Layer MoS ₂ Field Effect Transistors. <i>Advanced Electronic Materials</i> , 2020 , 6, 2000659	6.4	9
66	Understanding interface properties in 2D heterostructure FETs. <i>Semiconductor Science and Technology</i> , 2020 , 35, 103003	1.8	6
65	Tuning the inhomogeneous charge transport in ZnO interfaces for ultrahigh on/off ratio top-gated field-effect-transistor arrays. <i>Nano Research</i> , 2020 , 13, 3033-3040	10	1
64	Use of the Indirect Photoluminescence Peak as an Optical Probe of Interface Defectivity in MoS ₂ . <i>Advanced Materials Interfaces</i> , 2020 , 7, 2000413	4.6	4
63	Titanium disulfide as Schottky/ohmic contact for monolayer molybdenum disulfide. <i>Npj 2D Materials and Applications</i> , 2020 , 4,	8.8	6
62	Stacking the MoS ₂ /GeSe ₂ vertical van der Waals heterostructure for memory device. <i>Applied Physics Letters</i> , 2020 , 117, 153104	3.4	2
61	Transition from Hopping to Band-like Transport in Weakly Coupled Multilayer MoS ₂ Field Effect Transistors. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 971-979	4	3
60	Few-Layered MoS Field-Effect Transistors with a Vertical Channel of Sub-10 nm. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 32943-32950	9.5	9
59	Insulators for 2D nanoelectronics: the gap to bridge. <i>Nature Communications</i> , 2020 , 11, 3385	17.4	85
58	Synthesis of heterostructures based on two-dimensional materials. 2020 , 265-287		1
57	Computational insights into structural, electronic and optical characteristics of GeC/CN van der Waals heterostructures: effects of strain engineering and electric field.. <i>RSC Advances</i> , 2020 , 10, 2967-2974	3.7	7
56	Thermal History-Dependent Current Relaxation in hBN/MoS van der Waals Dimers. <i>ACS Nano</i> , 2020 , 14, 5909-5916	16.7	5
55	Surface-enhanced resonance Raman scattering of MoS ₂ quantum dots by coating Ag@MQDs on silver electrode with nanoscale roughness. <i>Journal of Luminescence</i> , 2021 , 230, 117704	3.8	3
54	Atomically Thin Hexagonal Boron Nitride and Its Heterostructures. <i>Advanced Materials</i> , 2021 , 33, e2000769	16.9	31
53	How good are 2D transistors? An application-specific benchmarking study. <i>Applied Physics Letters</i> , 2021 , 118, 030501	3.4	6
52	Moiré Superlattices and related moiré excitons in twisted van der Waals heterostructures. <i>Chemical Society Reviews</i> , 2021 , 50, 6401-6422	58.5	9
51	Enhanced Electrical Performance of Van der Waals Heterostructure. <i>Advanced Materials Interfaces</i> , 2021 , 8, 2001850	4.6	3
50	Tip-Based Cleaning and Smoothing Improves Performance in Monolayer MoS Devices. <i>ACS Omega</i> , 2021 , 6, 4013-4021	3.9	2

49	Van der Waals engineering of ferroelectric heterostructures for long-retention memory. <i>Nature Communications</i> , 2021 , 12, 1109	17.4	29
48	Reconfigurable electronics by disassembling and reassembling van der Waals heterostructures. <i>Nature Communications</i> , 2021 , 12, 1825	17.4	10
47	Direct Laser Patterning of a 2D WSe ₂ Logic Circuit. <i>Advanced Functional Materials</i> , 2021 , 31, 2009549	15.6	6
46	Selective Pattern Growth of Atomically Thin MoSe Films via a Surface-Mediated Liquid-Phase Promoter. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 18056-18064	9.5	3
45	Modeling and Understanding the Compact Performance of h-BN Dual-Gated ReS ₂ Transistor. <i>Advanced Functional Materials</i> , 2021 , 31, 2100625	15.6	7
44	Turn of the decade: versatility of 2D hexagonal boron nitride. <i>JPhys Materials</i> , 2021 , 4,	4.2	7
43	Traps at the hBN/WSe ₂ interface and their impact on polarity transition in WSe ₂ . <i>2D Materials</i> , 2021 , 8, 035027	5.9	2
42	Investigation of charge trapping mechanism in MoS ₂ field effect transistor by incorporating Al into host LaOAs gate dielectric. <i>Nanotechnology</i> , 2021 , 32,	3.4	1
41	Quantum tunneling in two-dimensional van der Waals heterostructures and devices. <i>Science China Materials</i> , 2021 , 64, 2359-2387	7.1	5
40	Systematic Design and Demonstration of Multi-Bit Generation in Layered Materials Heterostructures Floating-Gate Memory. <i>Advanced Functional Materials</i> , 2105472	15.6	2
39	Solution-Gated Ultrathin Channel Indium Tin Oxide-Based Field-Effect Transistor Fabricated by a One-Step Procedure that Enables High-Performance Ion Sensing and Biosensing. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 38569-38578	9.5	4
38	Gate-controlled MoTe ₂ homojunction for sub-thermionic subthreshold swing tunnel field-effect transistor. <i>Nano Today</i> , 2021 , 40, 101263	17.9	4
37	Ambipolar conduction and multicolor photosensing behaviors from poly(9,9-di-n-octylfluorenyl-2,7-diyl)-molybdenum disulfide heterointerfaces. <i>Surfaces and Interfaces</i> , 2021 , 27, 101448	4.1	2
36	When graphene meets white graphene - recent advances in the construction of graphene and h-BN heterostructures. <i>Nanoscale</i> , 2021 , 13, 13174-13194	7.7	3
35	ALD-ZrO ₂ gate dielectric with suppressed interfacial oxidation for high performance MoS ₂ top gate MOSFETs. <i>Japanese Journal of Applied Physics</i> , 2021 , 60, SBBH03	1.4	1
34	Hysteresis-reversible MoS ₂ transistor. <i>New Journal of Chemistry</i> , 2021 , 45, 12033-12040	3.6	3
33	Multistate Memory Enabled by Interface Engineering Based on Multilayer Tungsten Diselenide. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 58428-58434	9.5	10
32	Electrical characterization of 2D materials-based field-effect transistors. <i>2D Materials</i> , 2021 , 8, 012002	5.9	38

31	Strain enhancement for a MoS ₂ -on-GaN photodetector with an Al ₂ O ₃ stress liner grown by atomic layer deposition. <i>Photonics Research</i> , 2020 , 8, 799	6	17
30	Direct growth of hexagonal boron nitride films on dielectric sapphire substrates by pulsed laser deposition for optoelectronic applications. <i>Fundamental Research</i> , 2021 ,		3
29	Transistors based on two-dimensional materials for future integrated circuits. <i>Nature Electronics</i> , 2021 , 4, 786-799	28.4	51
28	Field-Dependent Band Structure Measurements in Two-Dimensional Heterostructures. <i>Nano Letters</i> , 2021 ,	11.5	0
27	Dielectric engineering enable to lateral anti-ambipolar MoTe ₂ heterojunction.. <i>Nanotechnology</i> , 2022 ,	3.4	1
26	The Low-Temperature Photocurrent Spectrum of Monolayer MoSe: Excitonic Features and Gate Voltage Dependence.. <i>Nanomaterials</i> , 2022 , 12,	5.4	1
25	Perspective of 2D Integrated Electronic Circuits: Scientific Pipe Dream or Disruptive Technology?. <i>Advanced Materials</i> , 2022 , e2201082	24	4
24	Constructing van der Waals heterostructures by dry-transfer assembly for novel optoelectronic device.. <i>Nanotechnology</i> , 2022 ,	3.4	0
23	Review-Hysteresis in Carbon Nano-Structure Field Effect Transistor.. <i>Micromachines</i> , 2022 , 13,	3.3	1
22	Unexpected Electron Transport Suppression in a Heterostructured Graphene-MoS Multiple Field-Effect Transistor Architecture.. <i>ACS Nano</i> , 2021 ,	16.7	0
21	Finding Suitable Gate Insulators for Reliable 2D FETs. 2022 ,		1
20	Stable Al ₂ O ₃ Encapsulation of MoS ₂ -FETs Enabled by CVD Grown h-BN. <i>Advanced Electronic Materials</i> , 2200123	6.4	1
19	High- κ Perovskite membranes as insulators for two-dimensional transistors.. <i>Nature</i> , 2022 , 605, 262-267	50.4	16
18	High-Temperature Stability Amorphous Ternary AlBN Dielectric Films on N ++ GaN. <i>Advanced Engineering Materials</i> , 2200191	3.5	0
17	Electrical characteristics of WSe ₂ transistor with amorphous BN capping layer. <i>Results in Physics</i> , 2022 , 38, 105568	3.7	0
16	Multilayer 2D insulator shows promise for post-silicon electronics. <i>Nature</i> , 2022 , 606, 37-38	50.4	
15	Epitaxial Growth of Crystalline CaF ₂ on Silicene. 2022 , 14, 32675-32682		0
14	Bilayer tungsten diselenide transistors with on-state currents exceeding 1.5 milliamperes per micrometre. 2022 , 5, 497-504		2

13	Raman imaging of strained bubbles and their effects on charge doping in monolayer WS ₂ encapsulated with hexagonal boron nitride. 2022 , 604, 154489	0
12	Challenges for Nanoscale CMOS Logic Based on Two-Dimensional Materials. 2022 , 12, 3548	1
11	High-Performance Monolayer MoS ₂ Field-Effect Transistors on Cyclic Olefin Copolymer-Passivated SiO ₂ Gate Dielectric. 2201653	0
10	Dielectrics for 2-D Electronics: From Device to Circuit Applications. 2022 , 1-25	1
9	Dielectric Material Technologies for 2-D Semiconductor Transistor Scaling. 2022 , 1-20	2
8	High performance 1D/2D CuO/MoS ₂ photodetectors enhanced by femtosecond laser-induced contact engineering.	0
7	High-Performance Solution-Processed 2D P-Type WSe ₂ Transistors and Circuits through Molecular Doping. 2208934	0
6	Wafer-scale integration of transition metal dichalcogenide field-effect transistors using adhesion lithography.	0
5	All-Optical Reconfigurable Excitonic Charge States in Monolayer MoS ₂ .	0
4	Two Dimensional Heterostructures for Optoelectronics: Current Status and Future Perspective. 2023 , 28, 2275	0
3	Self-Assembled TaOX/2H-TaS ₂ as a van der Waals Platform of a Multilevel Memristor Circuit Integrated with a β -Ga ₂ O ₃ Transistor. 2023 , 17, 3666-3675	0
2	Horizontal Arrays of One-Dimensional van der Waals Heterostructures as Transistor Channels. 2023 , 15, 10965-10973	0
1	Effect of Surface Modification on the Fundamental Electrical Characteristics of Solution-Gated Indium Tin Oxide-Based Thin-Film Transistor Fabricated by One-Step Sputtering. 2023 , 39, 4282-4290	0